

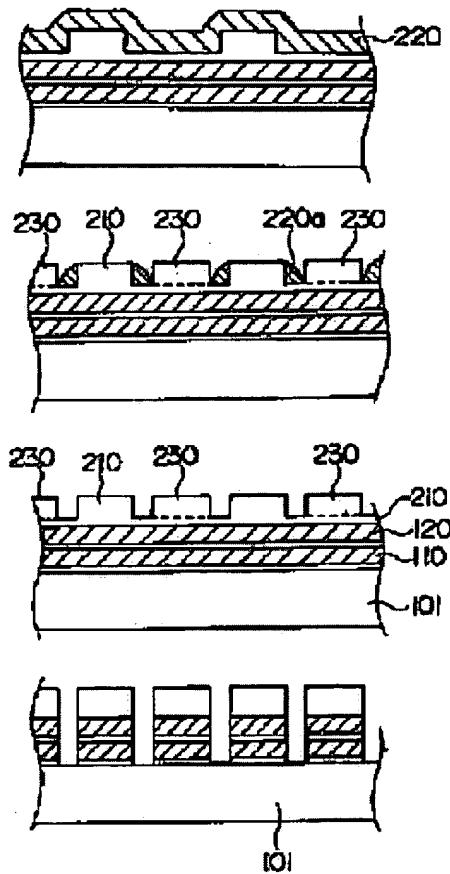
## MANUFACTURE OF SEMICONDUCTOR DEVICE

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- **european:**  
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### Abstract of JP5190809

**PURPOSE:** To make it possible to achieve high integration density by suppressing the effects of the machining-size errors and the position deviation of a photo- mask. **CONSTITUTION:** A nitride film 220 is formed on an SiO<sub>2</sub> film 210. The nitride film 220 is removed by anisotropic plasma etching so that the sidewall part of the SiO<sub>2</sub> film 210 remains. The nitride film, which remains at the sidewall part of the SiO<sub>2</sub> film 210, becomes a spacer 220a. Then, an SiO<sub>2</sub> film 230 is formed. At this time, the spacer 220 acts as a mask for forming the SiO<sub>2</sub>. The SiO<sub>2</sub> film 230 is formed at a part, where the spacer 220a is not present. The thick part of SiO<sub>2</sub> is used as an etching mask, and the etching is performed down to a polysilicon film 110. Thus a stack gate is formed.



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